# CSD87502Q2 30 V Dual N-Channel NexFET™ Power MOSFETs

## 1 Features

- Low On-Resistance
- Dual Independent MOSFETs
- Space Saving SON 2 × 2 mm Plastic Package
- Optimized for 5 V Gate Driver
- Avalanche Rated
- Pb and Halogen Free
- RoHS Compliant

## 2 Applications

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom, and Computing Systems
- Adaptor or USB Input Protection for Notebook PCs and Tablets
- Battery Protection

## 3 Description

The CSD87502Q2 is a 30 V, 27 mΩ N-Channel device with dual independent MOSFETs in a SON 2 x 2 mm plastic package. The two FETs were designed to be used in a half-bridge configuration for synchronous buck and other power supply applications. Additionally, these NexFET™ power MOSFETs can be used for adaptor, USB input protection, and battery charging applications. The dual FETs feature low drain-to-source on-resistance that minimizes losses and offers low component count for space-constrained applications.

### Product Summary

| $T_A$ = 25°C | | TYPICAL VALUE | | UNIT |
|---|---|---|---|---|
| $V_{DS}$ | Drain-to-Source Voltage | 30 | | V |
| $Q_g$ | Gate Charge Total (4.5 V) | 2.2 | | nC |
| $Q_{gd}$ | Gate Charge Gate to Drain | 0.5 | | nC |
| $R_{DS(on)}$ | Drain-to-Source On Resistance | $V_{GS}$ = 3.8 V | 42.0 | mΩ |
| | | $V_{GS}$ = 4.5 V | 35.5 | mΩ |
| | | $V_{GS}$ = 10 V | 27.0 | mΩ |
| $V_{GS(th)}$ | Threshold Voltage | 1.6 | | V |

### Ordering Information(1)

| DEVICE | MEDIA | QTY | PACKAGE | SHIP |
|---|---|---|---|---|
| CSD87502Q2 | 7-Inch Reel | 3000 | SON 2 x 2 mm Plastic Package | Tape and Reel |
| CSD87502Q2T | 7-Inch Reel | 250 | | |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

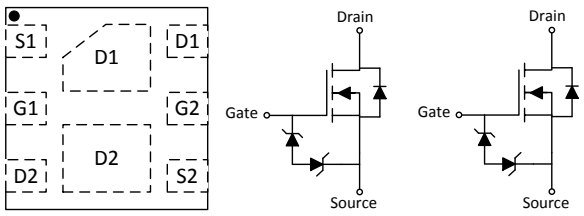
### Absolute Maximum Ratings

| $T_A$ = 25°C | | VALUE | UNIT |
|---|---|---|---|
| $V_{DS}$ | Drain-to-Source Voltage | 30 | V |
| $V_{GS}$ | Gate-to-Source Voltage | ±20 | V |
| $I_D$ | Continuous Drain Current (Package limited) | 5.0 | A |
| $I_{DM}$ | Pulsed Drain Current(1) | 23 | A |
| $P_D$ | Power Dissipation(2) | 2.3 | W |
| $T_J$, $T_{stg}$ | Operating Junction Temperature, Storage Temperature | –55 to 150 | °C |
| $E_{AS}$ | Avalanche Energy, single pulse $I_D$ = 7.9 A, L = 0.1 mH, $R_G$ = 25 Ω | 3.1 | mJ |

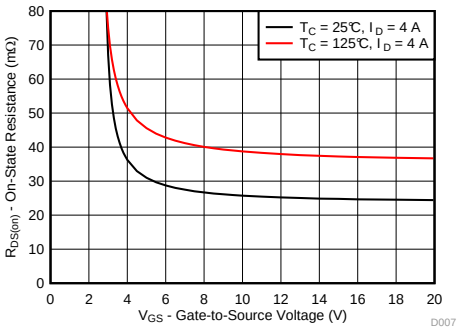
(1) Max $R_{\theta JA}$ = 185 °C/W, pulse duration ≤100 µs, duty cycle ≤1%.

(2) Typical $R_{\theta JA}$ = 55 °C/W on a 1 inch$^2$, 2 oz. Cu pad on a 0.06 inch thick FR4 PCB.

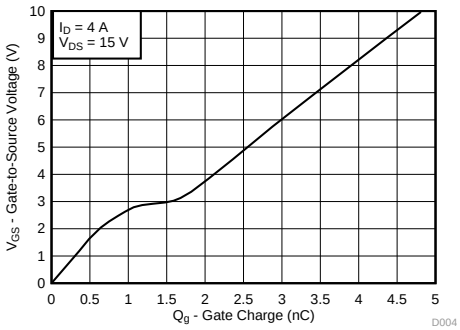
**Top View and Circuit Image**




**$R_{DS(on)}$ vs $V_{GS}$**




**Gate Charge**



# Table of Contents



## 4 Revision History

| DATE | REVISION | NOTES |
|---|---|---|
| December 2015 | * | Initial release. |

# 5 Specifications

## 5.1 Electrical Characteristics

($T_A$ = 25°C unless otherwise stated)

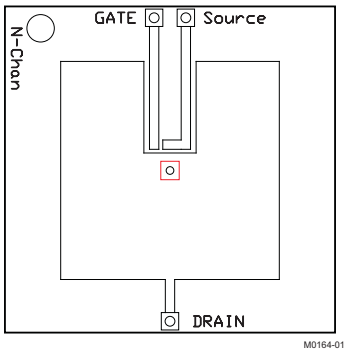
| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| **STATIC CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain-to-source voltage | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 30 | | | V |
| $I_{DSS}$ | Drain-to-source leakage current | $V_{GS}$ = 0 V, $V_{DS}$ = 24 V | | | 1 | µA |
| $I_{GSS}$ | Gate-to-source leakage current | $V_{DS}$ = 0 V, $V_{GS}$ = 20 V | | | 4 | µA |
| $V_{GS(th)}$ | Gate-to-source threshold voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 1.2 | 1.6 | 2.0 | V |
| $R_{DS(on)}$ | Drain-to-source on-resistance | $V_{GS}$ = 3.8 V, $I_D$ = 4 A | | 42.0 | 60.0 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 4 A | | 35.5 | 42.0 | mΩ |
| | | $V_{GS}$ = 10 V, $I_D$ = 4 A | | 27.0 | 32.4 | mΩ |
| $g_{fs}$ | Transconductance | $V_{DS}$ = 3 V, $I_D$ = 4 A | | 75 | | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{iss}$ | Input capacitance | $V_{GS}$ = 0 V, $V_{DS}$ = 15 V, $f$ = 1 MHz | | 272 | 353 | pF |
| $C_{oss}$ | Output capacitance | | | 42 | 55 | pF |
| $C_{rss}$ | Reverse transfer capacitance | | | 22 | 29 | pF |
| $R_G$ | Series gate resistance | | | 6.9 | | Ω |
| $Q_g$ | Gate charge total (4.5 V) | $V_{DS}$ = 15 V, $I_D$ = 4 A | | 2.2 | 2.9 | nC |
| $Q_g$ | Gate charge total (10 V) | | | 4.6 | 6.0 | nC |
| $Q_{gd}$ | Gate charge gate to drain | | | 0.5 | | nC |
| $Q_{gs}$ | Gate charge gate to source | | | 1.0 | | nC |
| $Q_{g(th)}$ | Gate charge at $V_{th}$ | | | 0.5 | | nC |
| $Q_{oss}$ | Output charge | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V | | 1.4 | | nC |
| $t_{d(on)}$ | Turn on delay time | $V_{DS}$ = 15 V, $V_{GS}$ = 5 V, $I_{DS}$ = 4 A, $R_G$ = 0 Ω | | 3 | | ns |
| $t_r$ | Rise time | | | 11 | | ns |
| $t_{d(off)}$ | Turn off delay time | | | 12 | | ns |
| $t_f$ | Fall time | | | 3 | | ns |
| **DIODE CHARACTERISTICS** | | | | | | |
| $V_{SD}$ | Diode forward voltage | $I_{SD}$ = 4 A, $V_{GS}$ = 0 V | | 0.85 | 1.0 | V |
| $Q_{rr}$ | Reverse recovery charge | $V_{DS}$= 15 V, $I_F$ = 4 A, di/dt = 300 A/µs | | 4.0 | | nC |
| $t_{rr}$ | Reverse recovery time | | | 6.4 | | ns |

## 5.2 Thermal Information

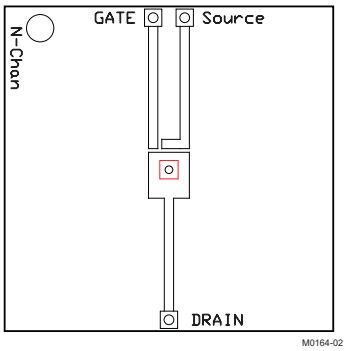
($T_A$ = 25°C unless otherwise stated)

| THERMAL METRIC | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance(1) | | | 70 | °C/W |
| | Junction-to-ambient thermal resistance(2) | | | 185 | |

(1) Device mounted on FR4 material with 1 inch$^2$ (6.45 cm$^2$), 2 oz. (0.071 mm thick) Cu.
(2) Device mounted on FR4 material with minimum Cu mounting area.




Max $R_{\theta JA}$ = 70 when mounted on 1 inch$^2$ (6.45 cm$^2$) of 2 oz. (0.071 mm thick) Cu.




Max $R_{\theta JA}$ = 185 when mounted on minimum pad area of 2 oz. (0.071 mm thick) Cu.

## 5.3 Typical MOSFET Characteristics

($T_A$ = 25°C unless otherwise stated)

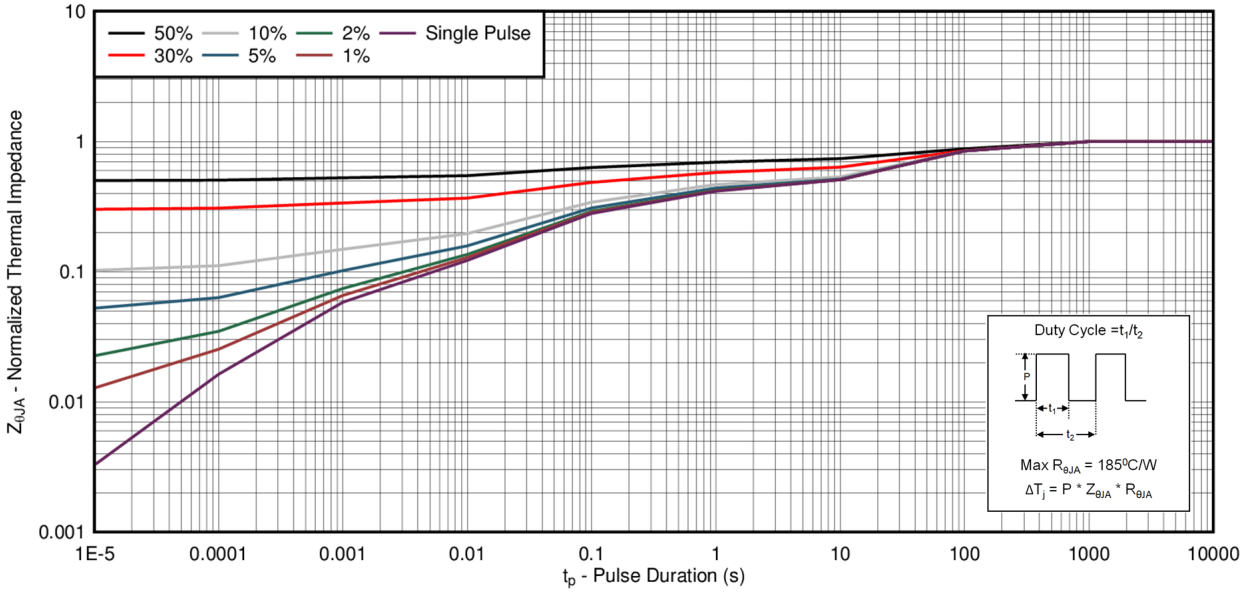



**Figure 1. Transient Thermal Impedance**

## Typical MOSFET Characteristics (continued)

($T_A$ = 25°C unless otherwise stated)

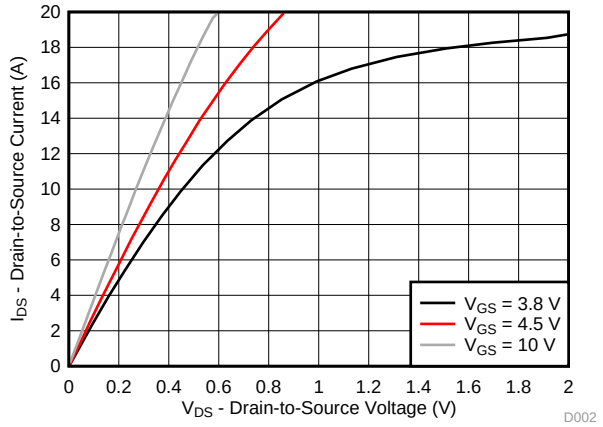



**Figure 2. Saturation Characteristics**

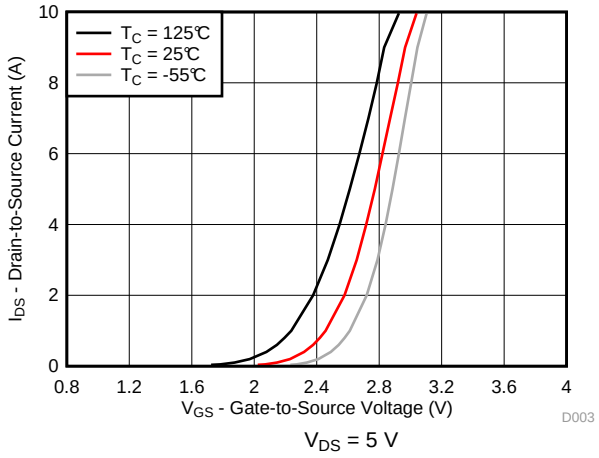



**Figure 3. Transfer Characteristics**

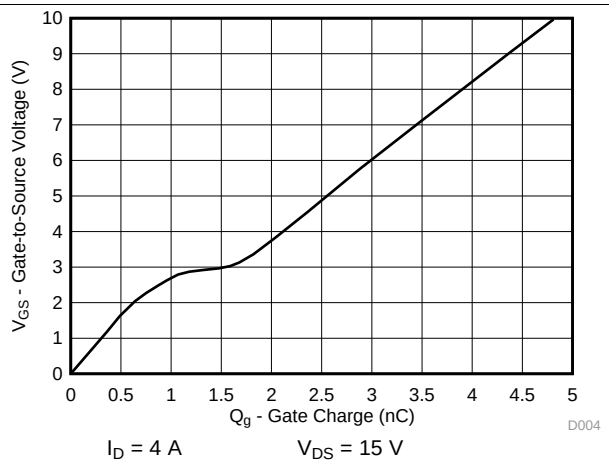



**Figure 4. Gate Charge**

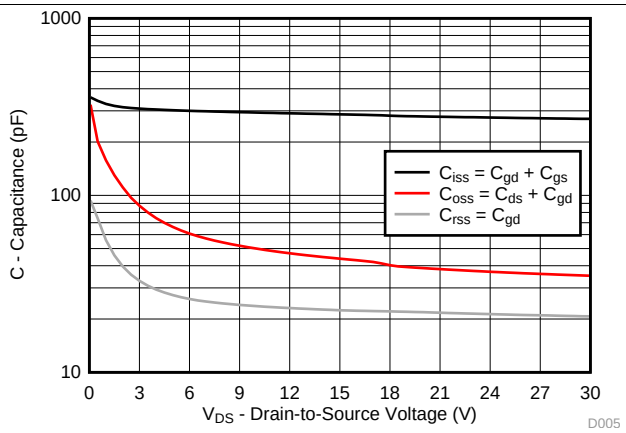



**Figure 5. Capacitance**

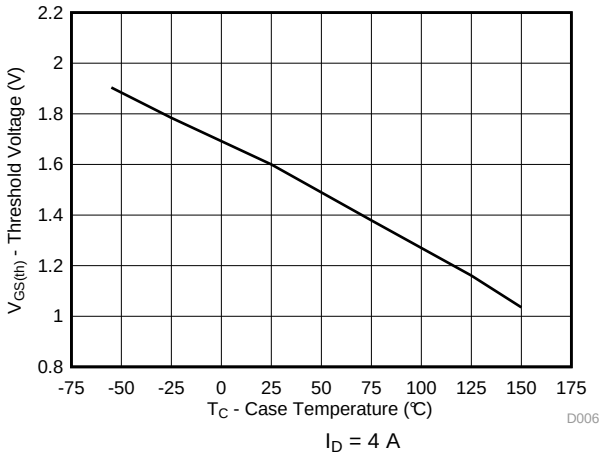



**Figure 6. Threshold Voltage vs Temperature**

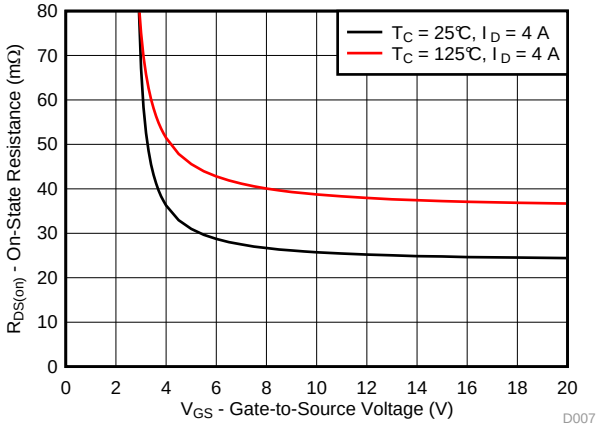



**Figure 7. On-State Resistance vs Gate-to-Source Voltage**

## Typical MOSFET Characteristics (continued)

($T_A$ = 25°C unless otherwise stated)

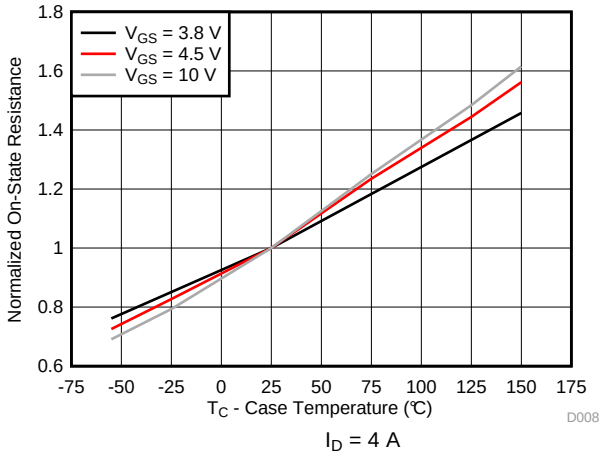



**Figure 8. Normalized On-State Resistance vs Temperature**

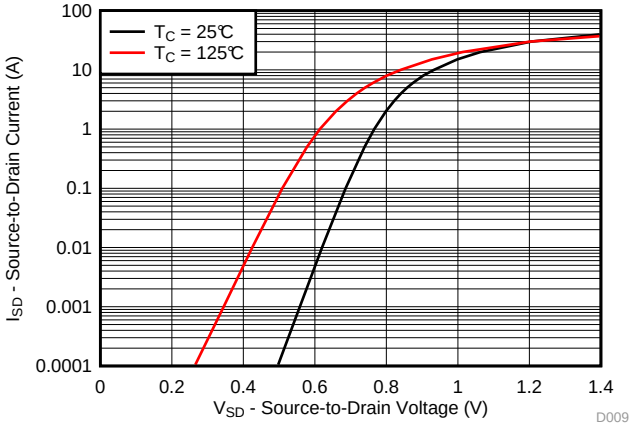



**Figure 9. Typical Diode Forward Voltage**

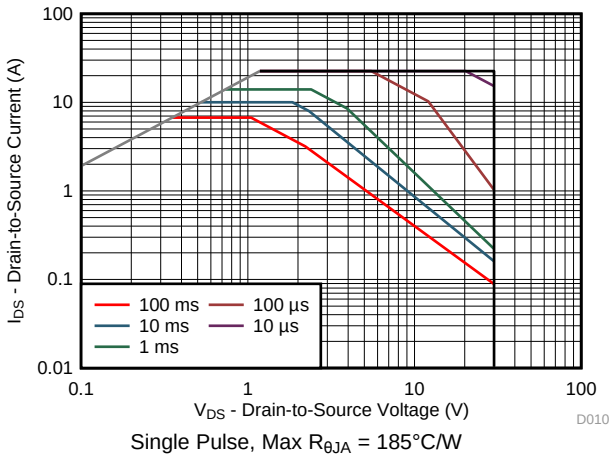



**Figure 10. Maximum Safe Operating Area**

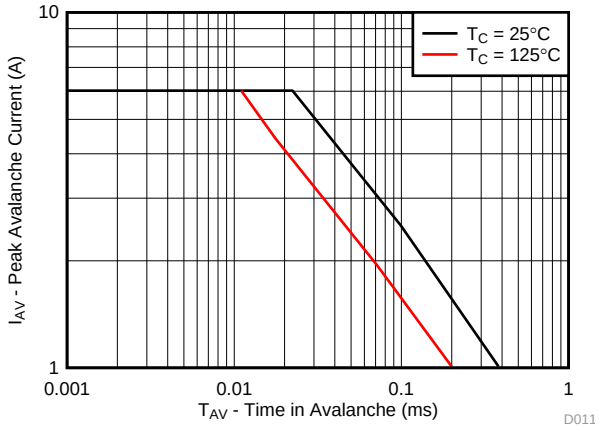



**Figure 11. Single Pulse Unclamped Inductive Switching**

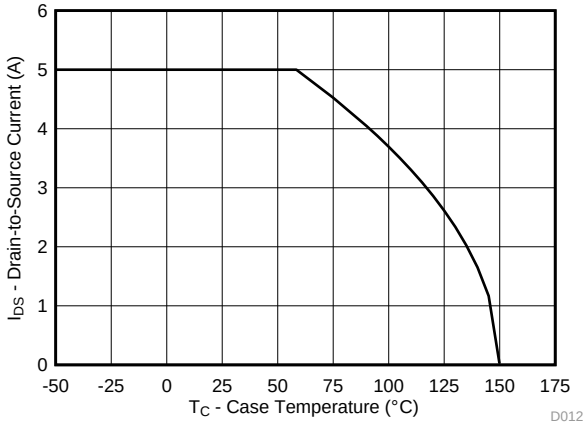



**Figure 12. Maximum Drain Current vs Temperature**

# 6 Device and Documentation Support

## 6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

**TI E2E™ Online Community** ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

## 6.2 Trademarks

NexFET, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

## 6.3 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 6.4 Glossary

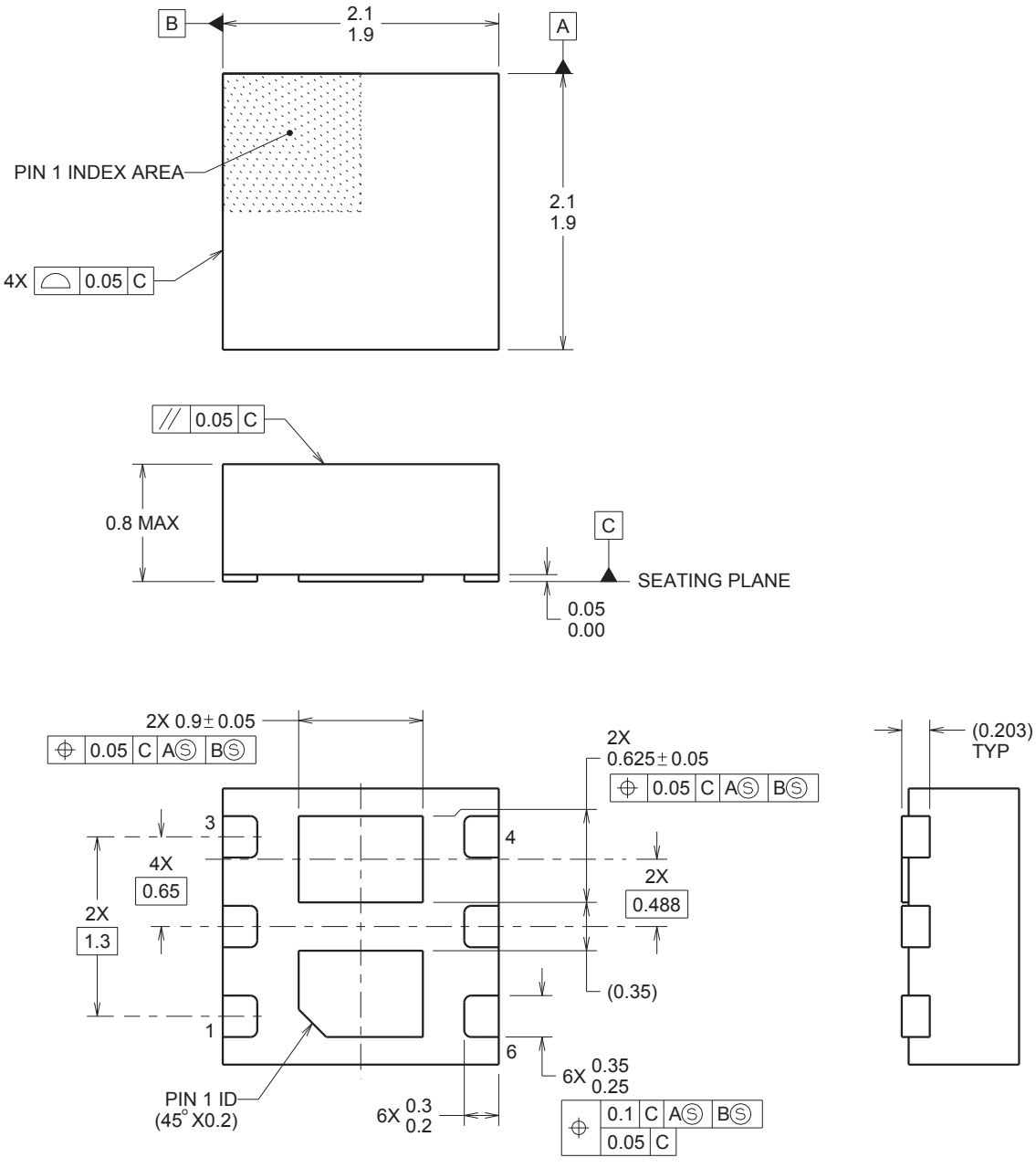
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

# 7 Mechanical, Packaging, and Orderable Information

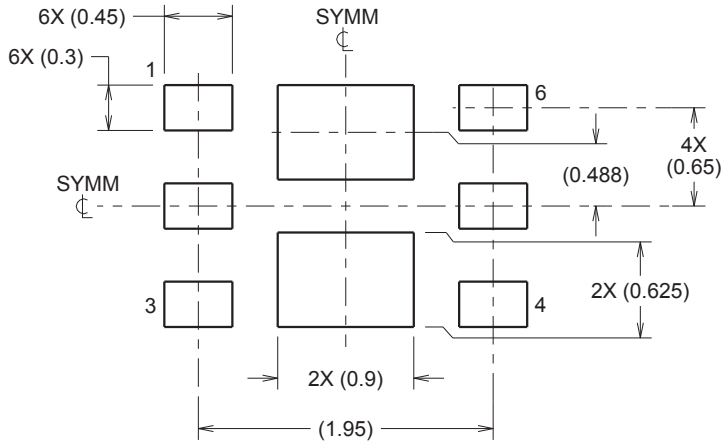
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## 7.1 Package Dimensions



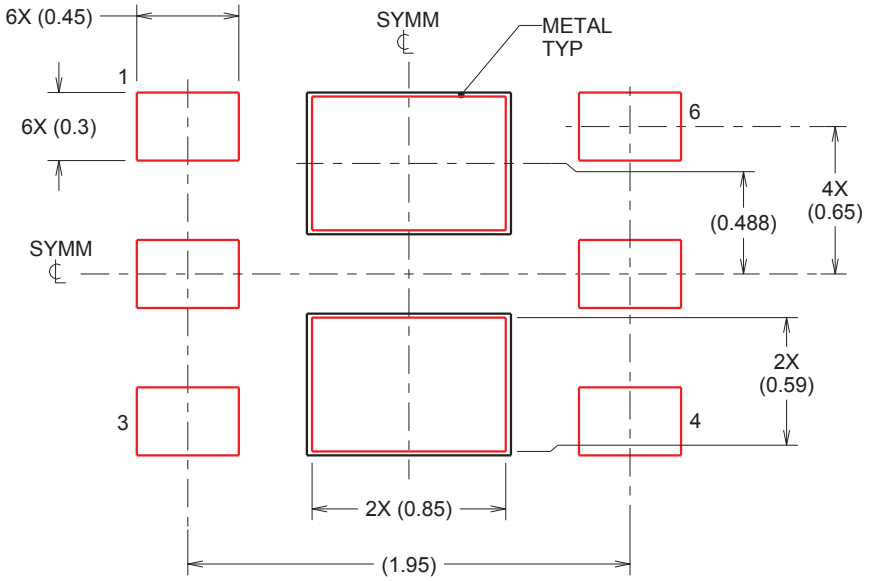

All dimensions are in mm, unless otherwise stated.

## 7.2 PCB Land Pattern



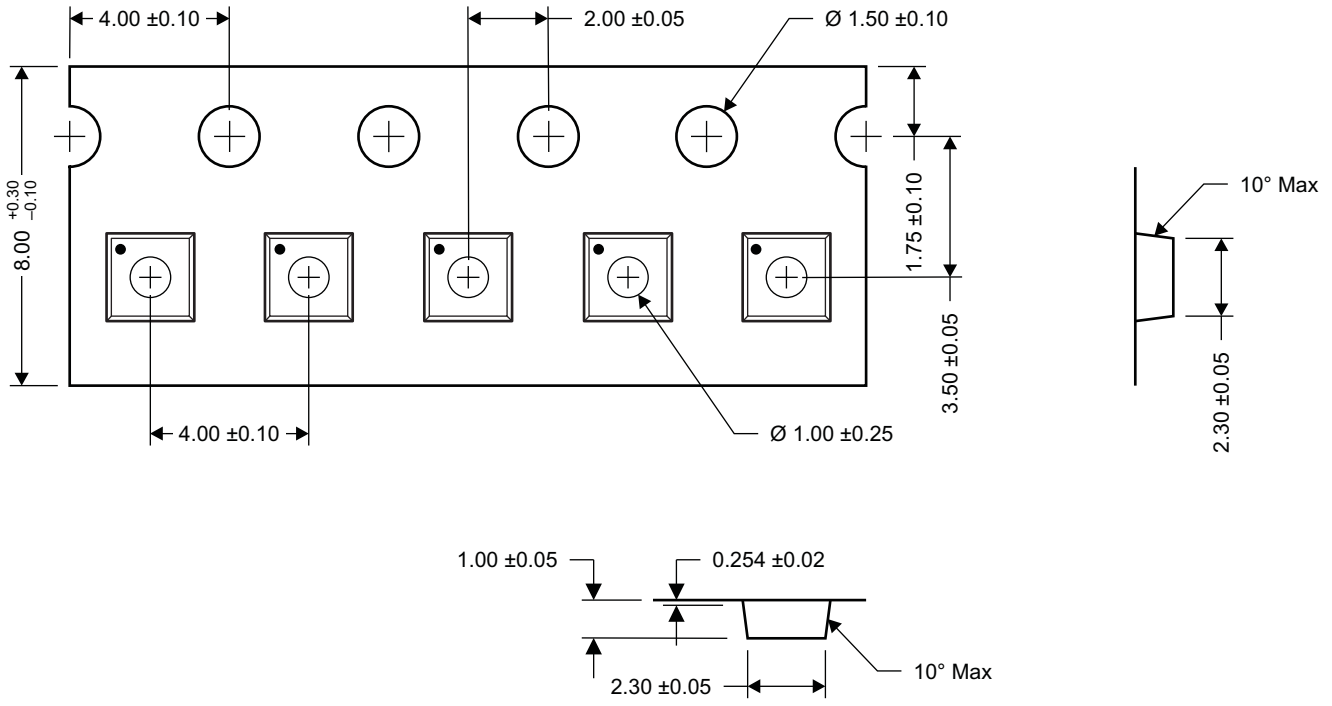

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

## 7.3 Recommended Stencil Opening




All dimensions are in mm, unless otherwise stated.

## 7.4 Q2 Tape and Reel Information




Notes:
1. Measured from centerline of sprocket hole to centerline of pocket
2. Cumulative tolerance of 10 sprocket holes is ±0.20
3. Other material available
4. Typical SR of form tape Max $10^9$ OHM/SQ
5. All dimensions are in mm, unless otherwise specified.

## PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead finish/ Ball material (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|---|---|---|---|---|---|---|---|---|---|---|---|
| CSD87502Q2 | ACTIVE | WSON | DLV | 6 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -55 to 150 | 8752 | Samples |
| CSD87502Q2T | ACTIVE | WSON | DLV | 6 | 250 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -55 to 150 | 8752 | Samples |

(1) The marketing status values are defined as follows:
**ACTIVE:** Product device recommended for new designs.
**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.
**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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